

Semiconductor Integrated circuit apparatus and its manufacturing method

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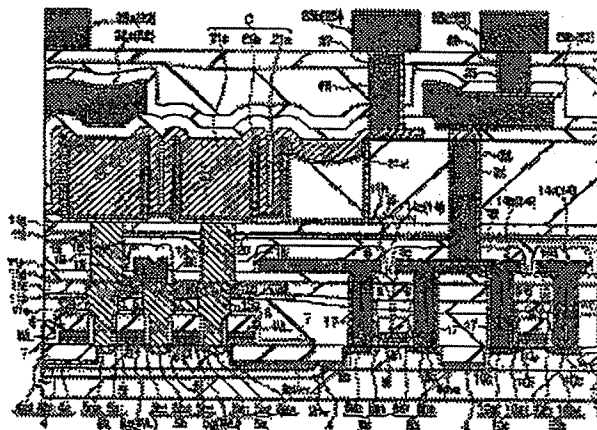
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The present invention relates to the semiconductor integrated circuit apparatus and its manufacturing method, in which the semiconductor integrated circuit apparatus is composed of MISFET and capacitor devices. In order to improve the refresh characteristic of memory cell, the conductivity type of low impedance polysilicon film of the gate electrode 5g for the n-channel MISFETQ, which is used for selecting the memory cell so as to composite the memory cells, is made to form p+ type.



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